

Gate Driver Providing Galvanic isolation Series

Isolation voltage 2500Vrms 1ch Gate Driver Providing Galvanic Isolation

BM60052FV-C

General Description

The BM60052FV-C is a gate driver with isolation voltage 2500Vrms, I/O delay time of 110ns, and a minimum input pulse width of 90ns. Fault signal output function, ready signal output function, under voltage lockout (UVLO) function, DESAT function, and switching controller function are all built-in.

Features

- Provides Galvanic Isolation
- Fault Signal Output Function
- Ready Signal Output Function
- Under Voltage Lockout Function
- DESAT Protection Function
- Soft Turn-Off Function for DESAT Protection (Adjustable Turn-OFF time)
- Thermal Protection Function
- Active Miller Clamping
- Switching Controller Function
- Output State Feedback Function
- UL1577 Recognized:File No. E356010
- AEC-Q100 Qualified^(Note 1) (Note 1:Grade1)

Applications

- Driving IGBT Gate
- Driving MOSFET Gate

Typical Application Circuit

Key Specifications

Isolation Voltage: 2500Vrms
 Maximum Gate Drive Voltage: 20V(Max)
 I/O Delay Time: 110ns(Max)
 Minimum Input Pulse Width: 90ns(Max)

 Package
 W(Typ) x D(Typ) x H(Max)

 SSOP-B28W
 9.2 mm x 10.4 mm x 2.4 mm

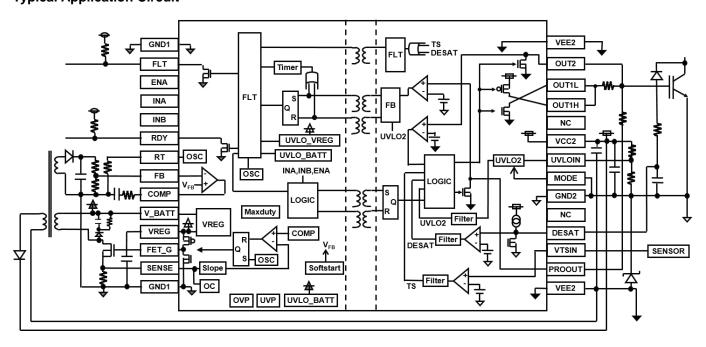


Figure 1. Typical Application Circuit

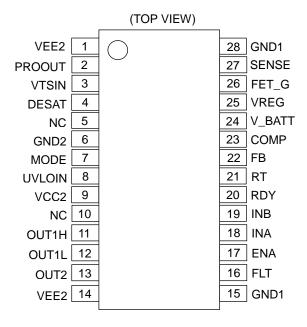
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Recommended Range of External Constants

Pin Name	Cymbol	Recon	Unit		
FIII Name	Symbol	Min	Тур	Max	Offic
VREG	CVREG	1.0	3.3	10.0	μF
VCC2	C _{VCC2}	0.33	-	-	μF
RT	R _{RT}	24	68	150	kΩ

Pin Configuration



Pin Descriptions

ions		
	Pin Name	Pin Function
1	VEE2	Output-side negative power supply pin
2	PROOUT	Soft turn-off pin / Gate voltage input pin
3	VTSIN	Thermal detection pin
4	DESAT	Desaturation protection pin
5	NC	No connection
6	GND2	Output-side ground pin
7	MODE	Mode selection pin of output-side UVLO
8	UVLOIN	Output-side UVLO setting pin
9	VCC2	Output-side positive power supply pin
10	NC	No connection
11	OUT1H	Source side output pin
12	OUT1L	Sink side output pin
13	OUT2	Output pin for Miller Clamp
14	VEE2	Output-side negative power supply pin
15	GND1	Input-side ground pin
16	FLT	Fault output pin
17	ENA	Input enabling signal pin
18	INA	Control input pin A
19	INB	Control input pin B
20	RDY	Ready output pin
21	RT	Switching frequency setting pin for switching controller
22	FB	Error amplifier inverting input pin for switching controller
23	COMP	Error amplifier output pin for switching controller
24	V_BATT	Main power supply pin
25	VREG	Input-side internal power supply pin
26	FET_G	MOS FET control pin for switching controller
27	SENSE	Current detection pin for switching controller
28	GND1	Input-side ground pin

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Main Power Supply Voltage	V _{BATT}	-0.3 to +40.0 ^(Note 2)	V
Output-Side Positive Supply Voltage	V _{CC2}	-0.3 to +24.0 ^(Note 3)	V
Output-Side Negative Supply Voltage	V _{EE2}	-15.0 to +0.3 ^(Note 3)	V
Maximum Difference Between Output-Side Positive and Negative Voltages	V _{MAX2}	30.0	V
INA, INB, ENA Pin Input Voltage	Vin	-0.3 to +7.0 ^(Note 2)	V
MODE Pin Input Voltage	V _{MODE}	-0.3 to +VCC2+0.3 or +24.0 ^(Note 3)	V
DESAT Pin Input Voltage	V _{DESAT}	-0.3 to +VCC2+0.3 or +24.0 ^(Note 3)	V
VTSIN Pin Input Voltage	V _{VTS}	-0.3 to +VCC2+0.3 or +24.0 ^(Note 3)	V
UVLOIN Pin Input Voltage	V _{UVLOIN}	-0.3 to +VCC2+0.3 or +24.0 ^(Note 3)	V
OUT1H, OUT1L Pin Output Current (Peak 10µs)	IOUT1PEAK	5.0 ^(Note 4)	Α
OUT2 Pin Output Current (Peak 10µs)	IOUT2PEAK	5.0 ^(Note 4)	А
PROOUT Pin Output Current (Peak 10µs)	IPROOUTPEA	2.5 ^(Note 4)	Α
FLT, RDY Pin Output Current	I _{FLT}	10	mA
FET_G Pin Output Current (Peak 1µs)	FET_GPEAK	1	А
Power Dissipation	Pd	1.12 ^(Note 5)	W
Operating Temperature Range	Topr	-40 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Junction Temperature	Tjmax	+150	°C

⁽Note 2) Relative to GND1

(Note 5) Derate above Ta=25°C at a rate of 9.5mW/°C. Mounted on a glass epoxy of 70 mm × 70 mm × 1.6 mm

Caution: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Main Power Supply Voltage ^(Note 6)	VBATT	4.0	32	V
Output-Side Positive Supply Voltage ^(Note 7)	V _{CC2}	10	20	V
Output-Side Negative Supply Voltage ^(Note 7)	V _{EE2}	-12	0	V
Maximum Difference Between Output-Side Positive and Negative Voltages	V _{MAX2}	10	28	V
Switching frequency for switching controller	fswr	100	500	kHz

(Note 6) Relative to GND1 (Note 7) Relative to GND2

Insulation Related Characteristics (UL1577)

Parameter	Symbol	Characteristic	Unit
Insulation Resistance (V _{IO} =500V)	Rs	>10 ⁹	Ω
Insulation Withstand Voltage / 1min	V _{ISO}	2500	Vrms
Insulation Test Voltage / 1sec	Viso	3000	Vrms

⁽Note 3) Relative to GND2

⁽Note 4) Should not exceed Pd and Tj=150°C

Electrical Characteristics

(Unless otherwise specified Ta=-40°C to +125°C, VBATT=4.0V to 32V, VCC2=UVLO to 20V, VEE2=-12V to 0V)

(Unless otherwise specified Ta=	Symbol	Min	Typ	Max	Unit	Conditions
General	Symbol	IVIII I	тур	IVIAX	Offic	Conditions
Main Power Supply						
Circuit Current 1	I _{BATT1}	1.1	1.6	2.1	mA	V_BATT=4.0V
Main Power Supply						
Circuit Current 2	I _{BATT2}	8.0	1.3	1.8	mA	V_BATT=12.0V
Main Power Supply						
Circuit Current 3	I _{BATT3}	0.8	1.3	1.8	mA	V_BATT=32.0V
Output Side Circuit Current 1	I _{CC21}	1.2	1.8	2.4	mA	Vcc2=14V, OUT1=L
Output Side Circuit Current 2	I _{CC22}	0.9	1.5	2.1	mA	Vcc2=14V, OUT1=H
Output Side Circuit Current 3	Icc23	1.3	1.9	2.5	mA	Vcc2=18V, OUT1=L
Output Side Circuit Current 4	I _{CC24}	1.0	1.6	2.2	mA	V _{CC2} =18V, OUT1=H
		4.4	0.0	0.0		V _{CC2} =16V, V _{EE2} =-8V,
Output Side Circuit Current 5	Icc25	1.4	2.0	2.6	mA	OUT1=L
0.4.40:1.0: "0.40		4.4	4.7	0.0		V _{CC2} =16V, V _{EE2} =-8V,
Output Side Circuit Current 6	I _{CC26}	1.1	1.7	2.3	mA	OUT1=H
Switching Power Supply Controll	er					•
FET_G Output Voltage H1	\/	2.0	4.0	4.0	V	4.2V <v_batt≤32v< td=""></v_batt≤32v<>
FE1_G Output voltage H1	V _{FETGH1}	3.8	4.0	4.2	V	I _{FET_G} =0A(open)
FET_G Output Voltage H2	V _{FETGH2}	_	V_BATT-0.2	V_BATT	V	V_BATT ≤ 4.2V
FE1_G Output voltage H2	VFEIGH2	-	V_BATT-0.2	V_DATT	V	I _{FET_G} =0A(open)
FET_G Output Voltage L	V _{FETGL}	0	-	0.3	V	I _{FET_G} =0A(open)
FET_G ON-Resistance	Rongh	3	6	12	Ω	10mA
(Source-side)	TONGH	3	O .	12	32	TOTILA
FET_G ON-Resistance	Rongl	0.3	0.6	1.3	Ω	10mA
(Sink-side)	TONGL	0.5	0.0	1.5	32	TOTILA
Oscillation Frequency	fsw	182	200	222	kHz	RT=68kΩ
Soft-start Time	tss	-	-	50	ms	
FB Pin Threshold Voltage	V _{FB}	1.47	1.50	1.53	V	
FB Pin Input Current	I _{FB}	-0.8	0	0.8	μΑ	
COMP Pin Sink Current	ICOMPSINK	-160	-80	-40	μΑ	
COMP Pin Source Current	ICOMPSOURCE	40	80	160	μΑ	
V_BATT UVLO ON Voltage	Vuvlobattl	3.20	3.40	3.60	V	
V_BATT UVLO Hysteresis	V _{UVLOBATTHYS}	0.07	0.1	0.13	V	
Maximum ON DUTY	DONMAX	-	48	-	%	
Over Voltage Detection Threshold	Vovth	1.60	1.65	1.70	V	
Under Voltage Detection Threshold	V_{UVTH}	1.23	1.30	1.37	V	
Over-Current Detection Threshold	Vостн	0.17	0.20	0.23	V	
Protection Holding Time	t _{DCDCRLS}	20	40	60	ms	
Logic Block	*DODOKES		10		1110	1
Logic High Level Input Voltage	Vinh	2.0	-	5.5	V	INA, INB, ENA
Logic Low Level Input Voltage	VINL	0	_	0.8	V	INA, INB, ENA
Logic Pull-Down Resistance	RIND	25	50	100	kΩ	INA, INB, ENA
Logic Input Filtering Time	t _{INFIL}	-	-	90	ns	INA, INB
ENA Input Filtering Time	tenafil	-	0.5	0.8	μs	ENA
MODE Low Level Input Voltage	V _{MODEL}	0	-	0.3×V _{CC2}	V	MODE, relative to GND2
	1		_			
MODE High Level Input Voltage	V _{MODEH}	0.7×V _{CC2}	-	V _{CC2}	V	MODE,relative to GND2

Electrical Characteristics – continued

			1			
Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Output			T	T		T
OUT1H ON-Resistance	Ronh	0.50	0.85	1.45	Ω	I _{OUT1H} =40mA
OUT1L ON-Resistance	R _{ONL}	0.25	0.45	0.80	Ω	I _{OUT1L} =40mA
OUT1 Maximum Current	I _{OUT1MAX}	3.0	4.5	-	Α	V _{CC2} =15V Design assurance
PROOUT ON-Resistance	Ronpro	0.45	0.85	1.55	Ω	I _{PROOUT} =40mA
Turn ON Time	t _{PONA}	45	75	105	ns	INA=PWM, INB=L
Turn ON Time	tPONB	50	80	110	ns	INA=H, INB=PWM
Turn OFF Times	t POFFA	40	70	100	ns	INA=PWM, INB=L
Turn OFF Time	t POFFB	35	65	95	ns	INA=H, INB=PWM
B	t PDISTA	-25	-5	15	ns	tpoffa – tpona
Propagation Distortion	t PDISTB	-35	-15	5	ns	tpoffb — tponb
Rise Time	trise	-	50	-	ns	10nF between OUT1-VEE2
Fall Time	tFALL	-	50	-	ns	Design assurance
OUT2 ON-Resistance	R _{ON2}	0.25	0.45	0.80	Ω	I _{OUT2} =40mA
OUT2 ON Threshold Voltage	V _{OUT2ON}	1.8	2	2.2	V	Relative to VEE2
Common Mode Transient Immunity	CM	100	-	-	kV/μs	Design assurance
Protection Functions						19
Output-side UVLO ON						
Threshold Voltage	V_{UVLOINL}	0.85	0.90	0.95	V	UVLOIN, MODE=L
Output-side UVLO Threshold		0.10×	0.11×	0.12×		
Hysteresis	Vuvloinhys	V _{UVLOINL}	V _{UVLOINL}	V _{UVLOINL}	V	UVLOIN, MODE=L
Output-side UVLO ON Voltage	V _{UVLO2L}	10.9	11.5	12.1	V	VCC2, MODE=H
Output-side UVLO Hysteresis	Vuvlo2hys	0.8	1.2	1.6	V	VCC2, MODE=H
Output-side UVLO	VOVEOZIIIS	0.0	1.2	1.0	,	
Filtering Time	tuvlo2fil	0.25	1.5	3.7	μs	
DESAT Charging Current	IDESATC	300	335	370	μA	V _{DESAT} =2V
DESAT Leading Edge	IDEG/(IO		333	0.0	la. r	· BESA II
Blanking Time	t _{DESATIeb}	0.14	0.20	0.26	μs	Design assurance
DESAT Threshold Voltage	VDESATDET	6.0	6.4	6.8	V	Relative to GND2
DESAT Filter Time	tdesatfil	0.12	0.2	0.28	μs	
DESAT Delay Time (PROOUT)	tDESATPRO	0.26	0.38	0.50	μs	
DESAT Low Voltage	VDESATL	-	0.1	0.22	V	I _{DESAT} =1mA
Output Delay Difference	* BEGATE		U	0.22		I DEGATI TITULE
between PROOUT and FLT	t PROFLT	0.1	0.4	0.7	μs	
Thermal Detection Voltage	VTSDET	1.61	1.70	1.79	V	Relative to GND2
Thermal Detection Filter Time	ttsfil	4	10	30	μs	TOMETO TO STEEL
Soft Turn Off Release Time	tsric tsro	30	-	110	μs	
FLT Output Low Voltage	V _{FLTL}	-	0.18	0.40	V	I _{FLT} =5mA
Gate State H Detection	V FLIL	=	0.10	0.70	· ·	11 - 011// (
Threshold Voltage	Vosfbh	4.5	5.0	5.5	V	Relative to GND2
Gate State L Detection					+	
Threshold Voltage	Vosfbl	4.0	4.5	5.0	V	Relative to GND2
OSFB Output Filtering Time	toorse	1.5	2.0	2.5	110	
	tosfbfil	ι.υ		1	μs	I
RDY Output Low Voltage	V_{RDYL}	-	0.18	0.40	V	I _{RDY} =5mA

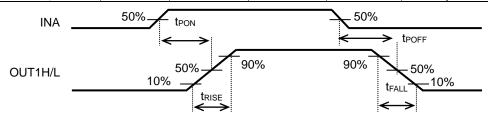


Figure 2. INA-OUT1H/L Timing Chart

UL1577 Ratings Table

Following values are described in UL Report.

Parameter	Values	Units	Conditions
Side 1 (Input Side) Circuit Current	1.3	mA	V_BATT=12V, OUT1H/L=L
Side 2 (Output Side) Circuit Current	2	mA	VCC2=18V, VEE2=-6V, OUT1H/L=L
Side 1 (Input Side) Consumption Power	15.6	mW	V_BATT=12V, OUT1H/L=L
Side 2 (Output Side) Consumption Power	48	mW	VCC2=18V, VEE2=-6V, OUT1H/L=L
Isolation Voltage	2500	Vrms	
Maximum Operating (Ambient) Temperature	125	°C	
Maximum Junction Temperature	150	°C	
Maximum Strage Temperature	150	°C	
Maximum Data Transmission Rate	5.5	MHz	

20

Typical Performance Curves

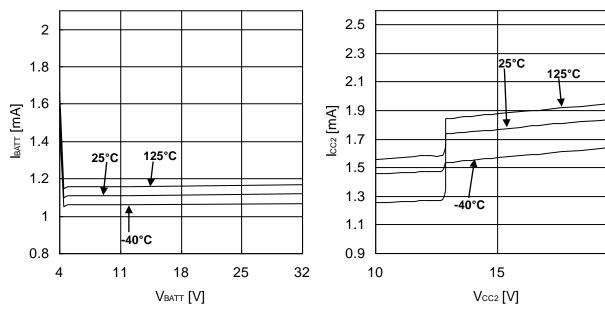


Figure 3. Main Power Supply Circuit Current

Figure 4. Output Side Circuit Current (MODE=H, VEE2=0V, OUT1=L)

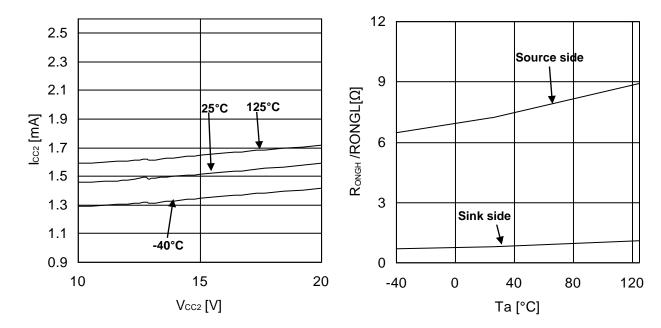


Figure 5. Output Side Circuit Current (MODE=H, VEE2=0V, OUT1=H)

Figure 6. FET_G ON-Resistance (Source side/Sink side)

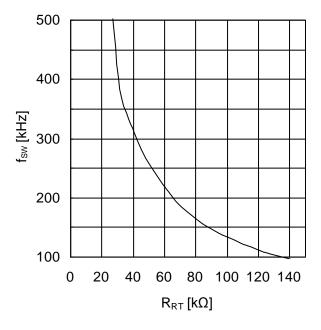


Figure 7. Oscillation Frequency

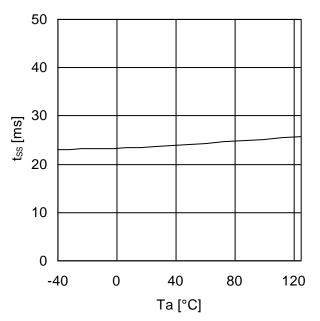


Figure 8. Soft-start Time

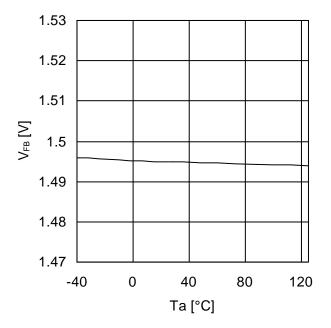


Figure 9. FB Pin Threshold Voltage

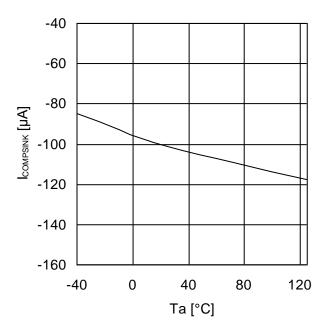


Figure 10. COMP Pin Sink Current

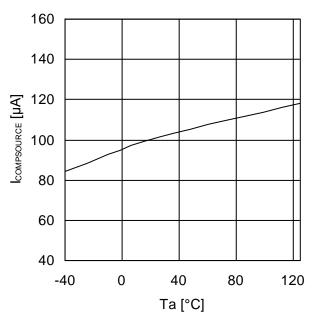


Figure 11. COMP Pin Source Current

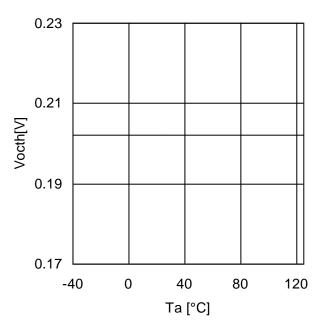


Figure 12. Over-Current Detection Threshold

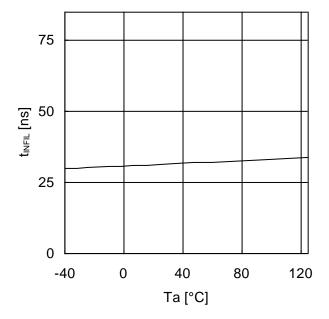


Figure 13. Logic Input Filtering Time (L pulse)

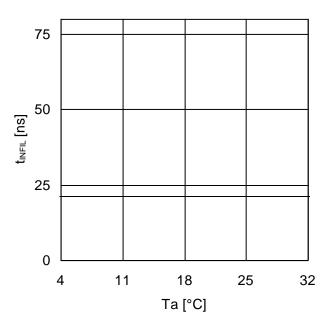


Figure 14. Logic Input Filtering Time (H pulse)

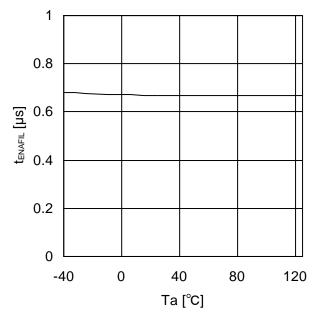


Figure 15. ENA Input Filtering Time

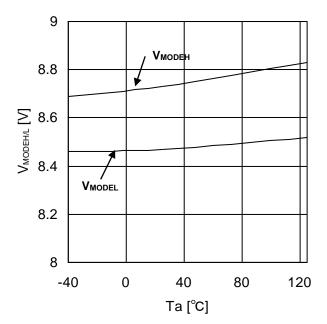


Figure 16. MODE Input Voltage H/L

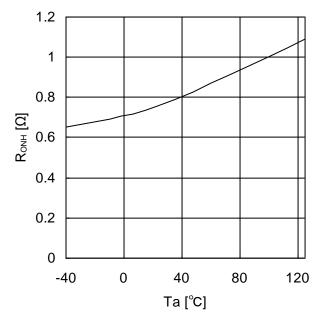


Figure 17. OUT1H ON-Resistance (Iout1=40mA)

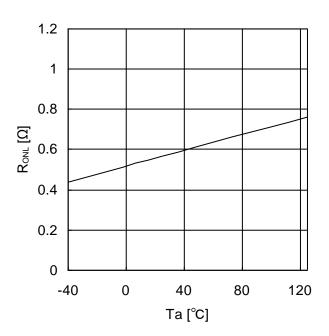


Figure 18. OUT1L ON-Resistance (Iout1=40mA)

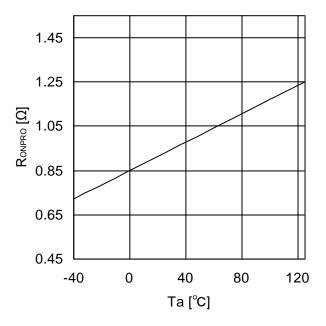


Figure 19. PROOUT ON-Resistance (IPROOUT=40mA)

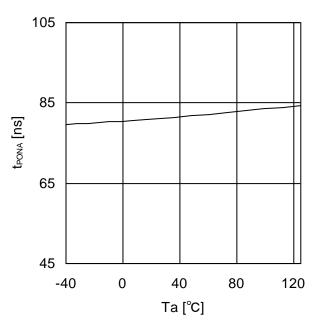


Figure 20. Turn ON time

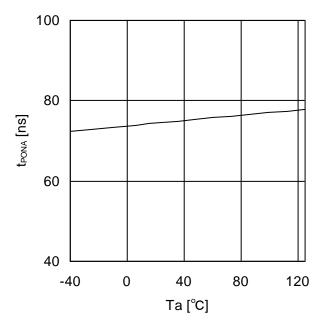


Figure 21. Turn OFF time

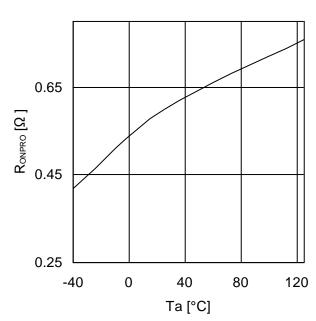
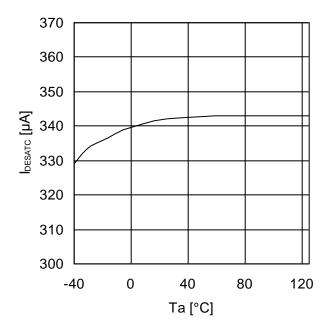


Figure 22. OUT2 ON-Resistance (Iout2=40mA)



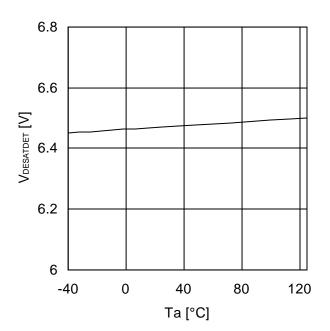


Figure 23. DESAT Charging Current

Figure 24. DESAT Threshold Voltage

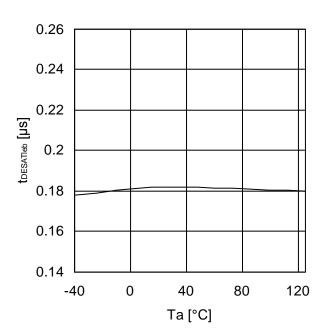


Figure 25. DESAT Leading Edge Blanking Time

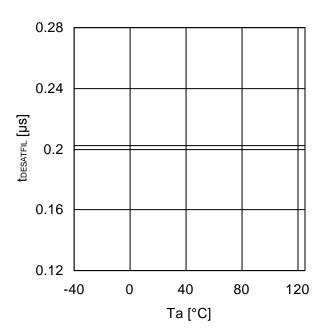
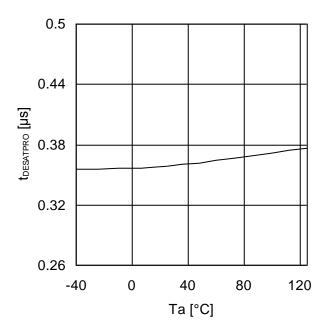


Figure 26. DESAT Filter Time



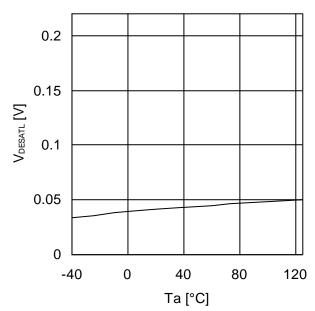


Figure 27. DESAT Delay Time (PROOUT)

Figure 28. DESAT Low Voltage

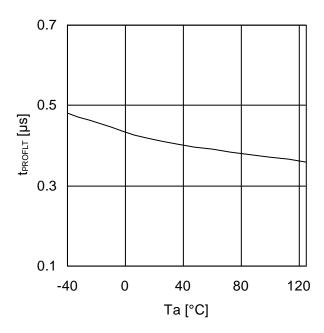


Figure 29. Output Delay Difference between PROOUT and FLT

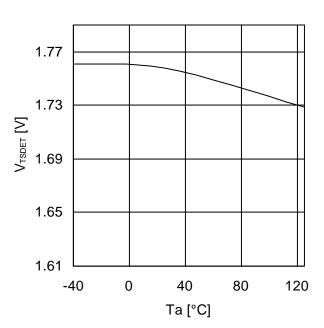


Figure 30. Thermal Detection Voltage

Application Information

1. Description of Pins and Cautions on Layout of Board

(1) V BATT (Main Power Supply Pin)

This is the main power supply pin. Connect a bypass capacitor between V_BATT and GND1 in order to suppress voltage variations.

(2) GND1 (Input-side Ground Pin)

The GND1 pin is a ground pin on the input side.

(3) VCC2 (Output-side Positive Power Supply Pin)

The VCC2 pin is a positive power supply pin on the output side. To reduce voltage fluctuations due to OUT1H/L pin output current and due to the driving current of the internal transformers, connect a bypass capacitor between VCC2 and GND2 pins.

(4) VEE2 (Output-side Negative Power Supply Pin)

The VEE2 pin is a power supply pin on the output side. To suppress voltage fluctuations due to OUT1H/L pin output current and due to the driving current of the internal transformers, connect a bypass capacitor between the VEE2 and the GND2 pins. Connect the VEE2 pin to the GND2 pin when no negative power supply is used,

(5) GND2 (Output-side Ground Pin)

The GND2 pin is a ground pin on the output side. Connect the GND2 pin to the emitter / source of a power device.

(6) INA, INB, ENA (Control Input Terminal)

The INA, INB, ENA are pins used to determine output logic.

ENA	INB	INA	OUT1H	OUT1L			
L	Χ	Χ	Hi-Z	L			
Н	Н	Χ	Hi-Z	L			
Н	L	L	Hi-Z	L			
Н	Ĺ	Н	Н	Hi-Z			

Fault state(FLT=L output) is released in rising of ENA(L→ H).

(7) FLT (Fault Output Pin)

The FLT pin is an open drain pin used to output a fault signal when desaturation function or thermal protection function is activated, and will be cleared at the rising edge of ENA.

, , , , , , , , , , , , , , , , , , , ,	
Status	FLT
While in normal operation	Hi-Z
When a fault occurs (When Desaturation or thermal protection is activated)	L

(8) RDY (Ready Output Pin)

The RDY pin shows the status of three internal protection features which are V_BATT UVLO, VCC2 UVLO, and output state feedback (OSFB). The term 'output state feedback' shows whether PROOUT pin voltage (High or Low) corresponds to input logic or not.

Status	RDY
While in normal operation	Hi-Z
V_BATT UVLO or VCC2 UVLO or Output state feedback	L

(9) MODE (Mode Selection Pin of Output-side UVLO)

The MODE pin is a pin which selects internal threshold or external setting threshold for output-side UVLO.

MODE	Output-side UVLO threshold voltage
L (=GND2)	Setting by external. (Use UVLOIN pin)
H (=VCC2)	Fixed (=VuvLo2L). (Connect UVLOIN pin to VCC2 pin)

(10) UVLOIN (Output-side UVLO Setting Input Pin)

The UVLOIN pin is a pin for deciding UVLO setting value of VCC2. The threshold value of UVLO can be set by dividing the resistance voltage of VCC2 and inputting such value. UVLOIN activates only at MODE pin=L. When MODE pin=H, connect UVLOIN pin to VCC2 pin.

(11) OUT1H, OUT1L(Output Pin)

The OUT1H pin is a source side pin used to drive the gate of a power device, and the OUT1L pin is a sink side pin used to drive the gate of a power device.

(12) OUT2 (Miller Clamp Pin)

This is the miller clamp pin for preventing a rise of gate voltage due to miller current of output element connected to OUT1. It also functions as a pin for monitoring gate voltage for miller clamp and OUT2 pin voltage become not more than VOUT2ON(typ 2.0V), miller clamp function operates. OUT2 should be connect to VEE2 when miller clamp function is not used.

(13) PROOUT (Soft Turn-OFF Pin)

This is a pin for soft turn-OFF of output pin when desaturation protection is in action. It also functions as a pin for monitoring gate voltage for output state feedback function.

(14) DESAT(Desaturation Protection Pin)

The DESAT pin is a pin used to detect desaturation of IGBT/MOSFET. When the DESAT pin voltage exceeds V_{DESAT}, the DESAT function will be activated. This may cause the IC to malfunction in an open state. To avoid such trouble, short-circuit the DESAT pin to the GND2 pin when the desaturation protection is not used. In order to prevent the wrong detection due to noise, the noise mask time t_{DESATFIL} is set.

(15) VTSIN (Thermal Detection Pin)

The VTSIN pin is a temperature sensor voltage input pin, which can be used for thermal protection of an output device. If VTSIN pin voltage becomes V_{TSDET} or less, OUT1H/L pin is set to HiZ/L. IC may malfunction in the open status, so be sure to supply the VTSPIN more than V_{TSDET} if the thermal protection function is not used. In order to prevent the wrong detection due to noise, the noise mask time t_{TSMSK} is set. In addition, it can be used also as compulsive shutdown terminal other than a temperature sense by inputting a comparator output etc.

(16) RT (Switching Frequency Setting Pin for Switching Controller)

The RT pin is a pin used to make setting of switching frequency of switching controller. The switching frequency is determined by the resistance value connected between RT and GND1. The value of switching frequency is determined by the value of the resistor R_{RT} .

$$F_{SW}[kHz] = 1/(7.3 \times 10^{-8} \times R_{RT} + 2.2 \times 10^{-4})$$

(17) FB (Error Amplifier Inverting Input Pin for Switching Controller)

This is a voltage feedback pin of the switching controller. This pin combine with voltage monitoring at overvoltage protection function and under voltage protection function for switching controller. When overvoltage or under voltage protection is activated, switching controller will be at OFF state (FET_G pin outputs Low). When the protection holding time (tdcdcrss) is completed, the protection function will be released. Under voltage function is not activated during soft-start.

(18) COMP (Error Amplifier Output Pin for Switching Controller)

This is the gain control pin of the switching controller. Connect a phase compensation capacitor and resistor.

(19) VREG (Input-side internal power supply pin)

This is the input-side internal power supply pin. Be sure to connect a capacitor between VREG and GND1 even when the switching controller is not used, in order to prevent oscillation and suppress voltage variation due to FET_G output current.

(20) FET G (MOS FET Control Pin for Switching Controller)

This is a MOSFET control pin for the switching controller transformer drive.

(21) SENSE (Connection to the Current Feedback Resistor of the Switching Controller)

This is a pin connected to the resistor of the switching controller current feedback. This pin combines with current monitoring at overcurrent protection function for switching controller. When overcurrent protection is activated, switching controller will be at OFF state (FET_G pin outputs Low). When the protection holding time (tdcdcrls) is completed, the over-current function will be released.

2. Description of Functions and Examples of Constant Setting

(1) Miller Clamp Function When OUT1=L and OUT2 pin voltage < V_{OUT2ON}, internal MOS of OUT2 pin is turned ON and miller clamp function operates.

IN	OUT2 pin input voltage	OUT2
L	Not more than V _{OUT2ON}	L
Н	X	Hi-Z

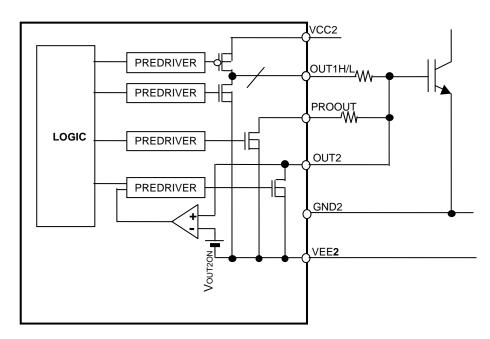


Figure 31. Block Diagram of Miller Clamp Function

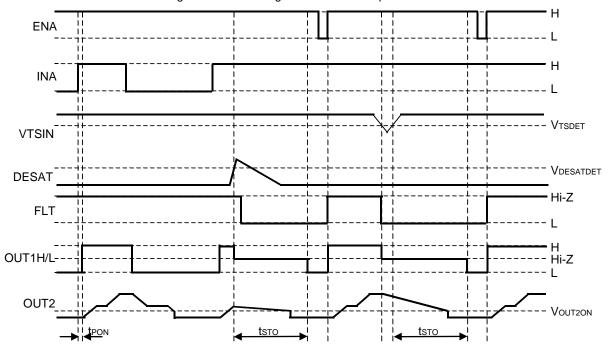


Figure 32. Timing Chart of Miller Clamp Function

(2) Under Voltage Lockout (UVLO) Function

The BM60052FV-C incorporates the under voltage lockout (UVLO) function on V_BATT and VCC2. When the power supply voltage drops to the UVLO ON voltage, the OUT1H/L pin will output the "Hi-Z / L" and the FLT pin will output the "L" signal. When the power supply voltage rises to the UVLO OFF voltage, these pins will be reset. In addition, to prevent mis-triggers due to noise, mask time tuvlobattfil and tuvlozfil are set on both voltage sides.

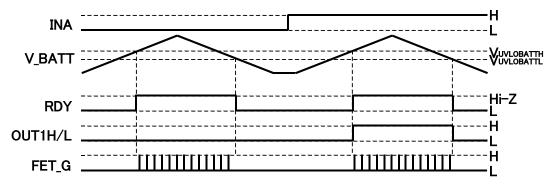


Figure 33. VBATT UVLO Function Operation Timing Chart

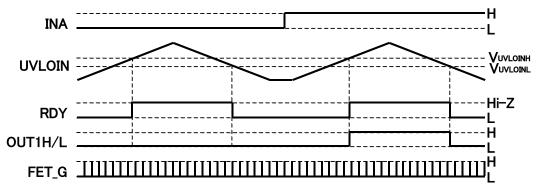


Figure 34. VCC2 UVLO Function Operation Timing Chart (MODE=L)

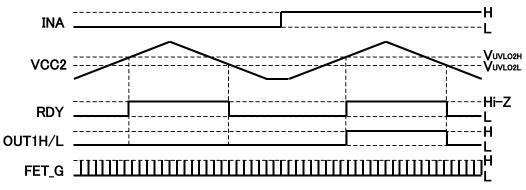


Figure 35. VCC2 UVLO Function Operation Timing Chart (MODE=H)

(3) Desaturation Protection Function (DESAT)

When the DESAT pin voltage exceeds \dot{V}_{DESAT} , the DESAT function will be activated. When the DESAT protection function is activated, the OUT1H/L pin voltage will be set to the "Hi-Z/Hi-Z" level and the PROOUT pin voltage will go to the "L" level first (soft turn-OFF). Next, After t_{STO} has passed, OUT1H/L pin become Hi-Z/L (PROOUT pin hold L). In addition, when OUT2 pin voltage < V_{OUT2ON} , miller clamp function operates.

When the rising edge is put in the ENA pin, the DESAT function will be released.

When OUT1H/L=Hi-Z/L or Hi-Z/Hi-Z, internal MOSFET connected to DESAT pin turns ON to discharge C_{BLANK}. When OUT1H/L=H/Hi-Z, internal MOSFET connected to DESAT pin turns OFF.

Blanking time (t_{BLANK}) can be calculated by the formula below;

$$t_{\text{BLANKoutemal}} \big[s \big] = \frac{C_{\text{BLANK}} \times V_{\text{DESATDET}}}{I_{\text{DESATC}}} + t_{\text{DESATIeb}}$$

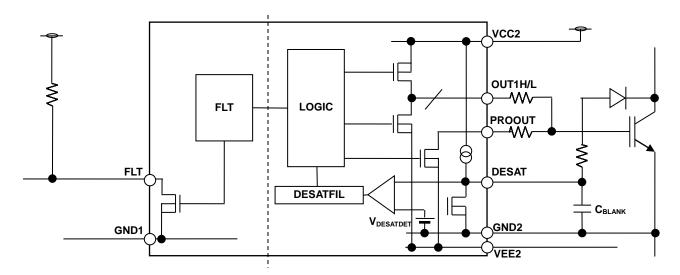


Figure 36. Block Diagram for DESAT

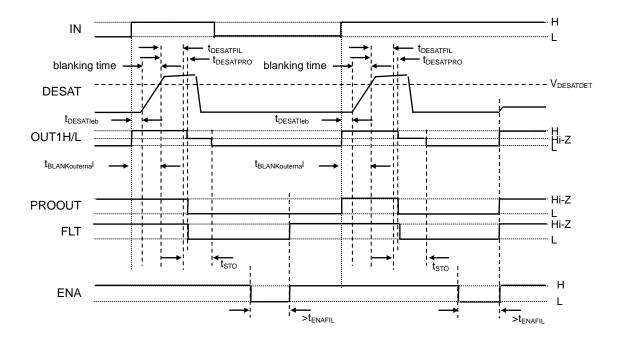


Figure 37. DESAT Operation Timing Chart

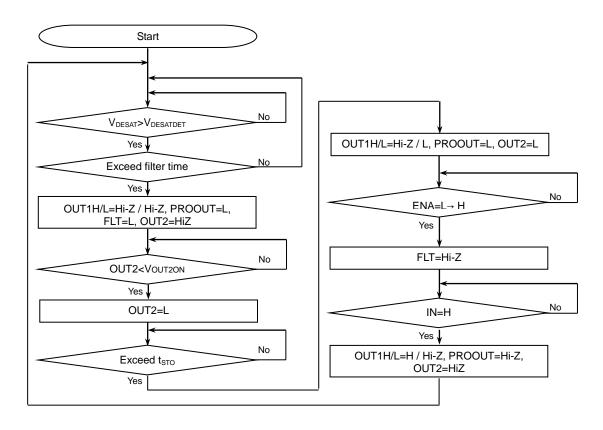


Figure 38. DESAT Operation Status Transition Diagram

(4) Thermal Protection Function

When the VTSIN pin voltage becomes V_{TSDET} or less, the thermal protection function will be activated. When the thermal protection function is activated, the OUT1H/L pin voltage will be set to the "Hi-Z/Hi-Z" level and the PROOUT pin voltage will go to the "L" level first (soft turn-OFF). Next, when the VTSIN pin voltage rises to the threshold value and after t_{STO} has passed, OUT1H/L pin become Hi-Z/L (PROOUT pin hold L). In addition, when OUT2 pin voltage < V_{OUT2ON} , miller clamp function operates.

When the rising edge is put in the ENA pin, the thermal protection function will be released.

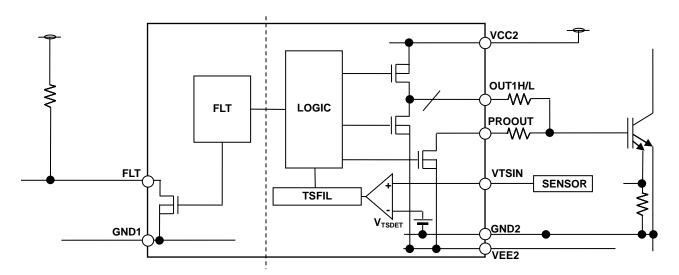


Figure 39. Block Diagram of thermal protection function

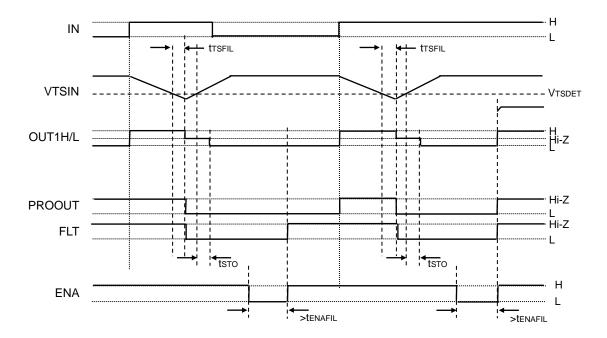


Figure 40. Thermal Protection Function Operation Timing Chart

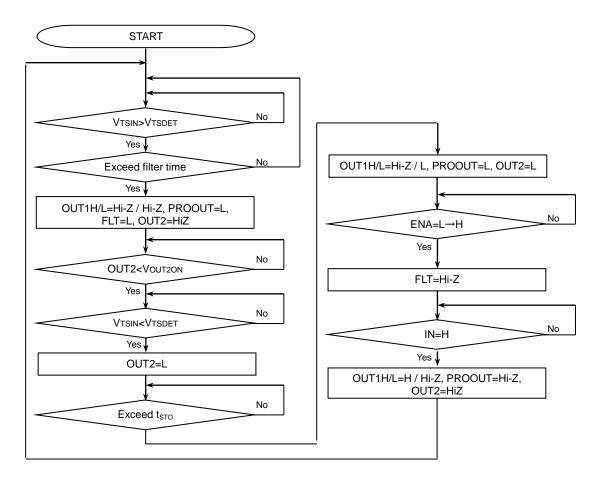


Figure 41. Thermal Protection Function Operation Status Transition Diagram

(5) Switching Controller

(a) Basic action

This IC has a built-in switching power supply controller which repeats ON/OFF synchronizing with internal clock set by RT pin. When VBATT voltage is supplied (VBATT > $V_{UVLOBATTH}$), FET_G pin starts switching by soft-start. Output voltage is determined by the following equation by external resistance and winding ratio "n" of flyback transformer (n= V_{OUT2} side winding number/ V_{OUT1} side winding number)

$$V_{OUT_2} = V_{FB} \times \{ (R_1 + R_2)/R_2 \} \times n[V]$$

(b) MAX DUTY

When, for example, output load is large, and voltage level of SENSE pin does not reach current detection level, output is forcibly turned OFF by Maximum On Duty (Donmax).

(c) Protection function

The switching controller has protection function as overvoltage protection (OVP), under voltage protection (UVP), and over-current protection (OCP). OVP and UVP monitor the voltage of FB pin, OCP monitor the voltage of SENSE pin.

When the protection function is activated, switching controller will be OFF state (FET_G pin outputs Low). The protection holding time (tdcdcRLs) is completed, the protection function will be released. Under voltage function is not activated during soft-start.

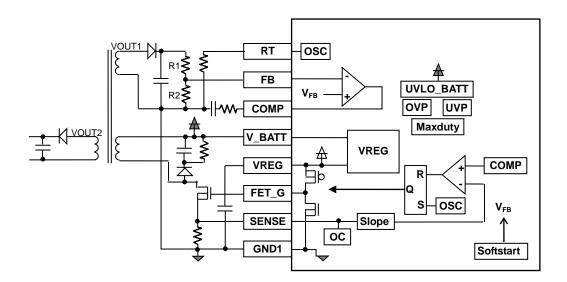


Figure 42. Block Diagram of switching controller

(d) The pin handling when not using switching controller

When not using switching controller, please do pin handling as follows.

When not using switching control	ier, piease do piri riaridiling as ioliows.	
pin no.	pin name	processing method
21	RT	pull down in gnd1 by 68kΩ
22	FB	connect to VREG
23	COMP	connect to VREG
24	V_BATT	connect power supply
25	VREG	connect capacitor
26	FET_G	open
27	SENSE	connect to VREG

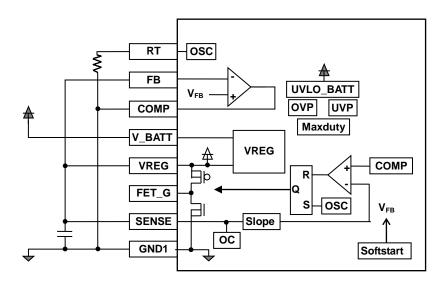


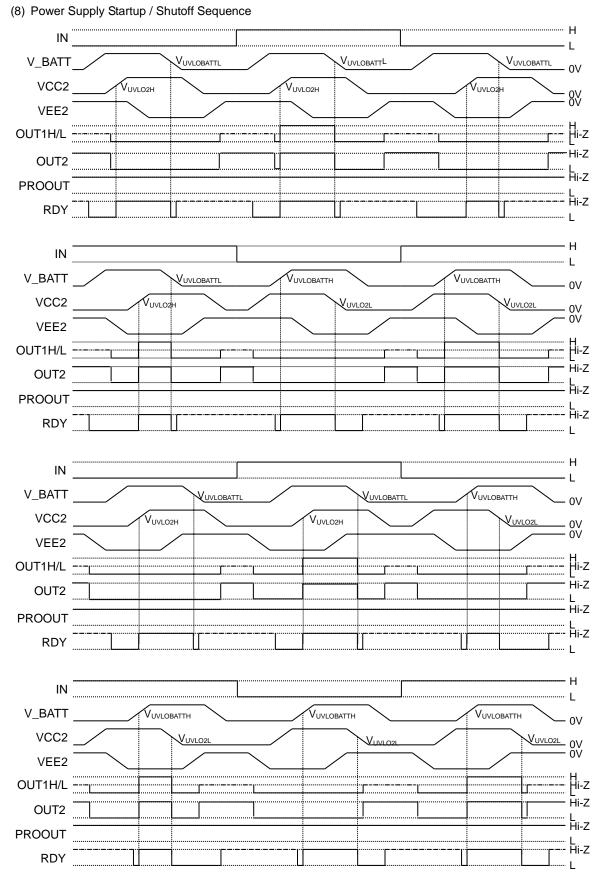
Figure 43. The pin handling when not using switching controller

(6) Gate State Monitoring Function

When gate logic and input logic of output device monitored with PROOUT pin are compared, a logic L is output from RDY pin when they disaccord. In order to prevent the detection error due to delay of input and output, OSFB filter time tosephile is provided.

((7) I/O Condition Table															
			Input						Output							
No.	Status	V B A T T	V C C 2	D E S A T	>	E N A	I N B	I N A	O U T 2	PROOUT	O U T 1 H	O U T 1 L	O U T 2	P R O O U T	F L T	R D Y
1	DESAT	0	0	Н	Η	Η	L	Н	Н	Χ	Hi-Z	Hi-Z	Hi-Z	L	L	Hi-Z
2	DESAI	0	0	Ι	Ι	Ι	L	Н	L	Χ	Hi-Z	Hi-Z	L	L	L	Hi-Z
3	UVLO_VBATT	UVLO	0	L	Ι	Χ	Χ	Х	Н	Ι	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
4	OVLO_VBATT	UVLO	0	L	Η	Χ	Χ	Х	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	L
5	5	0	UVLO	L	Ι	Χ	Χ	Х	Н	Ι	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
6	UVLO_VCC2	0	UVLO	L	Ι	Χ	Χ	Χ	L	Ш	Hi-Z	L	+	Hi-Z	Hi-Z	L
7	Thermal	0	0	L	L	Χ	Χ	Х	Н	Χ	Hi-Z	Hi-Z	Hi-Z	L	L	Hi-Z
8	protection	0	0	L	L	Χ	Χ	Х	L	Χ	Hi-Z	Hi-Z	L	L	L	Hi-Z
9	Disable	0	0	L	Ι	L	Χ	Х	Н	Ι	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
10	Disable	0	0	L	Η	L	Χ	Χ	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	Hi-Z
11	INB active	0	0	L	Ι	Ι	Ι	Х	Н	Ι	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
12	IND active	0	0	L	Ι	Ι	Ι	Χ	L	Ш	Hi-Z	L	L	Hi-Z	Hi-Z	Hi-Z
13	Normal Operation	0	0	L	Η	Η	L	L	Н	Η	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
14	L Input	0	0	L	Η	Η	L	L	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	Hi-Z
15	Normal Operation	0	0	L	Н	Η	L	Н	Н	Н	Н	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z
16	1.1.1		0	L	Н	Н	L	Н	L	L	Н	Hi-Z	Hi-Z	Hi-Z	Hi-Z	L

○ : > UVLO, X:Don't care



-----: : Since the VCC2 to VEE2 pin voltage is low and the output MOS does not turn ON, the output pins become Hi-Z conditions.

Figure 44. Power Supply Startup / Shutoff Sequence

[:] Since the VCC1 to GND1 pin voltage is low and the RDY output MOS does not turn ON, the output pins become Hi-Z conditions.

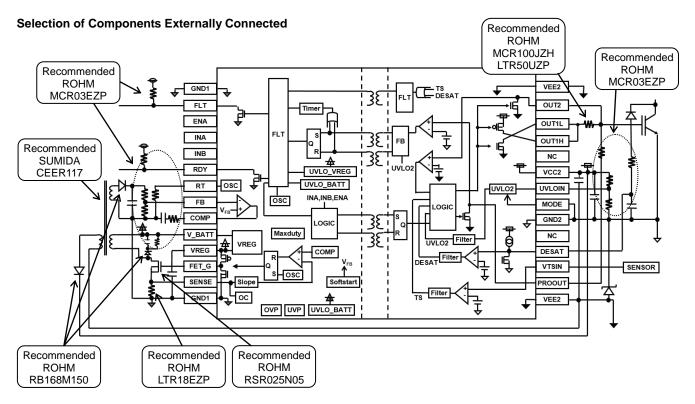


Figure 45. Recommended External Parts

Power Dissipation

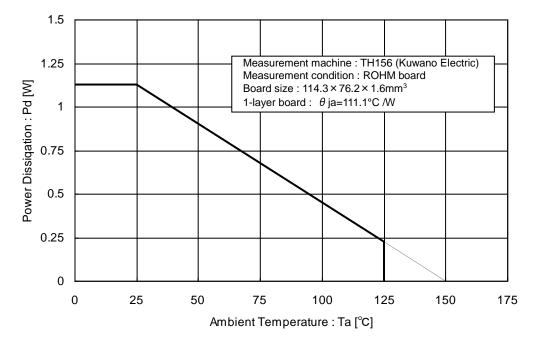


Figure 46. SSOP-B28W Derating Curve

Thermal Design

Please make sure that the IC's chip temperature Tj is not over 150°C, while considering the IC's power consumption (W), package power (Pd) and ambient temperature (Ta). When Tj=150°C is exceeded, the IC may malfunctions or some problems (ex. abnormal operation of various parasitic elements and increasing of leak current) may occur. Constant use under these circumstances leads to deterioration and eventually IC may destruct. Tjmax=150°C must be strictly obeyed under all circumstances.

O Equiva	lence Circuits Pin Name				
Pin No.	Pin Function	Input Output Equivalent Circuit Diagram			
2	PROOUT	VCC2			
	Soft turn-off pin / Gate voltage input pin	VEE2			
3	VTSIN	VCC2			
3	Thermal detection pin	VTSIN GND2			
4	DESAT	VCC2			
	Desaturation protection pin	DESAT GND2			
7	MODE	VCC2 MODE			
,	Mode selection pin of output-side UVLO	GND2 VEE2			
8	UVLOIN	VCC2			
	Output-side UVLO setting pin	GND2 VEE2			

Pin No.	Pin Name	Input Output Equivalent Circuit Diagram					
1 111 140.	Pin Function						
44	очт1н	—_ ♦ → ∨CC2					
11	Source side output pin	OUT1L					
12	OUT1L	VEE2					
	Sink side output pin						
13	OUT2	VCC2					
	Output pin for Miller Clamp	VEE2					
	FLT						
16	Fault output pin	FLT RDY					
	RDY						
20	Ready output pin	GND1					
	ENA	VREG					
47		ENA O					
17	Input enabling signal pin	GND1					

5: N	Pin Name	
Pin No.	Pin Function	Input Output Equivalent Circuit Diagram
18	INA	VREG O
	Control input pin A	GND1
19	INB	INB O
	Control input pin B	GND1
21	RT	V_BATT O
21	Switching frequency setting pin for switching controller	VEE2 VEE2
22	FB	V_BATT Internal power supply FB
	Error amplifier inverting input pin for switching controller	GND1

Pin No.	Pin Name	Input Output Equivalent Circuit Diagram		
1 110.	Pin Function			
23	СОМР	V_BATT Internal power supply COMP		
	Error amplifier output pin for switching controller	GND1		
25	VREG	Internal power V_BATT		
23	Input-side internal power supply pin	supply VREG		
	FET_G	FET_G		
26	MOS FET control pin for switching controller	GND1		
	SENSE	V_BATT Internal power supply		
27	Current detection pin for switching controller	SENSE WHO SENSE		

Operational Notes

1. Reverse Connection of Power Supply

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Thermal Consideration

Should by any chance the power dissipation rating be exceeded, the rise in temperature of the chip may result in deterioration of the properties of the chip. The absolute maximum rating of the Pd stated in this specification is when the IC is mounted on a 70mm x 70mm x 1.6mm glass epoxy board. In case of exceeding this absolute maximum rating, increase the board size and copper area to prevent exceeding the Pd rating.

6. Recommended Operating Conditions

These conditions represent a range within which the expected characteristics of the IC can be approximately obtained. The electrical characteristics are guaranteed under the conditions of each parameter.

7. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

8. Operation Under Strong Electromagnetic Field

Operating the IC in the presence of a strong electromagnetic field may cause the IC to malfunction.

9. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

10. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

11. Unused Input Terminals

Input terminals of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input terminals should be connected to the power supply or ground line.

Operational Notes - continued

12. Regarding Input Pins of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode.

When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

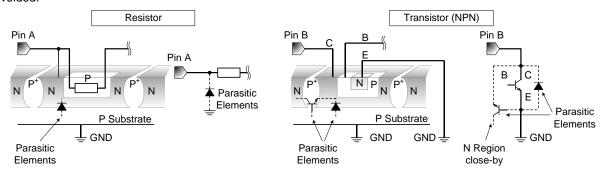
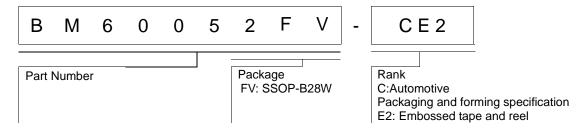


Figure 47. Example of Monolithic IC Structure

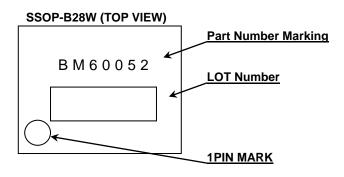
13. Ceramic Capacitor

When using a ceramic capacitor, determine the dielectric constant considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

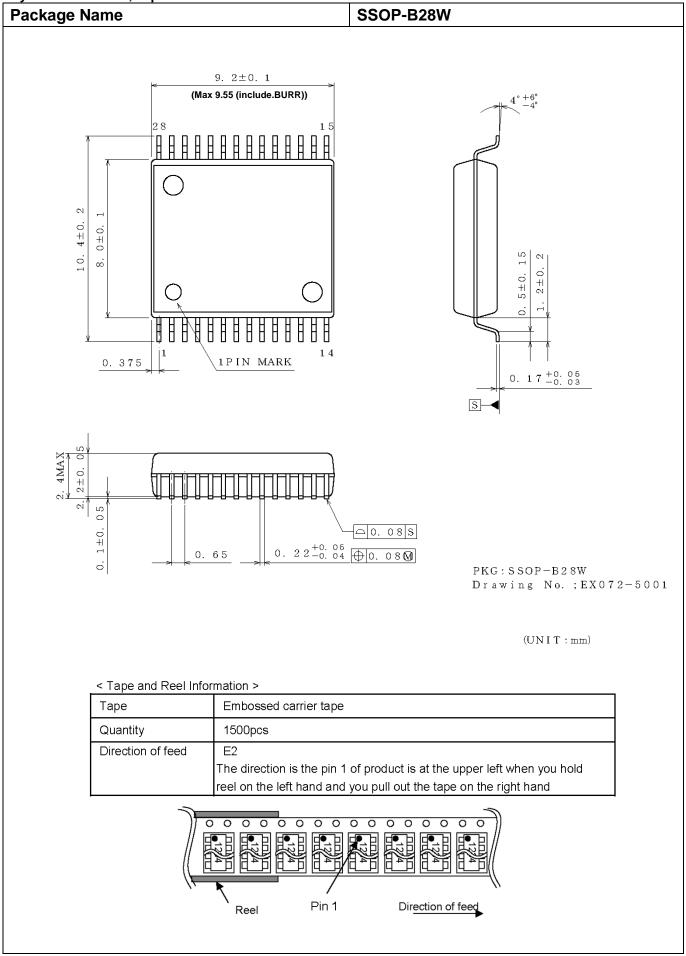
Ordering Information



Marking Diagram



Physical Dimension, Tape and Reel Information



Revision History

Date	Revision	Changes			
9.Apr.2015	001	New Release			
25.Dec.2015	002	Page 7 Adding UL1577 Rating Table Page15 Misprint correction of Description of Pins and Cautions on Layout of Board (7)FLT Page17 Misprint correction of Description of Functions and Examples of Constant Setting (1)Miller Clamp Function			

Notice

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JAPAN	USA	EU	CHINA
CLASSⅢ	OL ACOM	CLASS II b	ОГУООШ
CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

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 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - If Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
 may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
 exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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BM60052FV-C - Web Page

Part Number	BM60052FV-C
Package	SSOP-B28W
Unit Quantity	1500
Minimum Package Quantity	1500
Packing Type	Taping
Constitution Materials List	inquiry
RoHS	Yes